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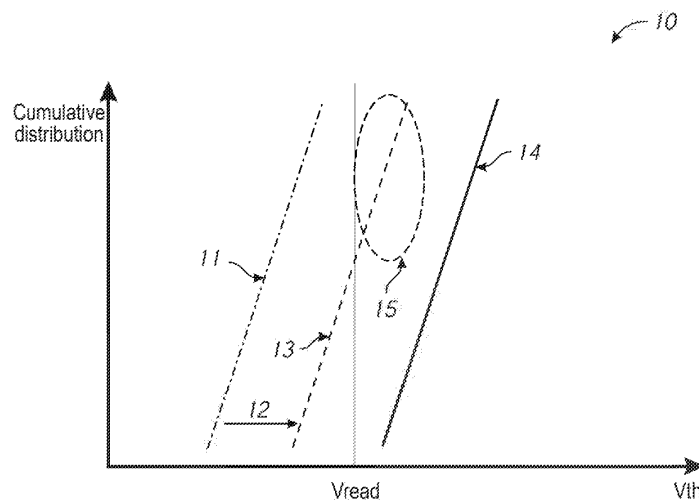


FIG. 1

(57) Abstract: Disclosed herein is a memory cell including a memory element and a selector device. The memory cell may be programmed with a programming pulse having a first polarity and read with a read pulse having a second polarity. The memory cell may be programmed with a programming pulse having first and second portions. The first and second portions may have different magnitudes and polarities. The memory cell may exhibit reduced voltage drift and/or threshold voltage distribution. Described herein is a memory cell that acts as both a memory element and a selector device. The memory cell may be programmed with a programming pulse having first and second portions. The first and second portions may have different magnitudes and polarities.

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